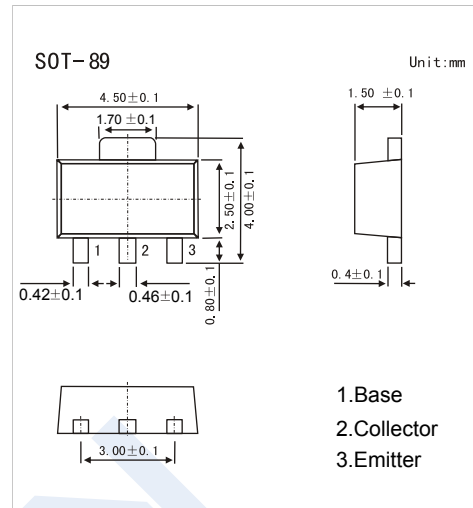


## PNP Transistors

## 2SB1132



### Features

- Low  $V_{CE(sat)}$
- Complies to 2SD1664

### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                        | Symbol    | Rating      | Unit             |
|----------------------------------|-----------|-------------|------------------|
| Collector-Base Voltage           | $V_{CBO}$ | -40         | V                |
| Collector-Emitter Voltage        | $V_{CEO}$ | -32         | V                |
| Emitter-Base Voltage             | $V_{EBO}$ | -5          | V                |
| Collector Current (DC)           | $I_c$     | -1          | A                |
| Single pulse, $P_w=100\text{ms}$ |           | -2          | A                |
| Collector Power Dissipation      | $P_C$ *   | 0.5         | W                |
| Junction temperature             | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature Range        | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

\* When mounted on a 40x40x0.7mm ceramic board.

### Electrical Characteristics $T_a = 25^\circ\text{C}$

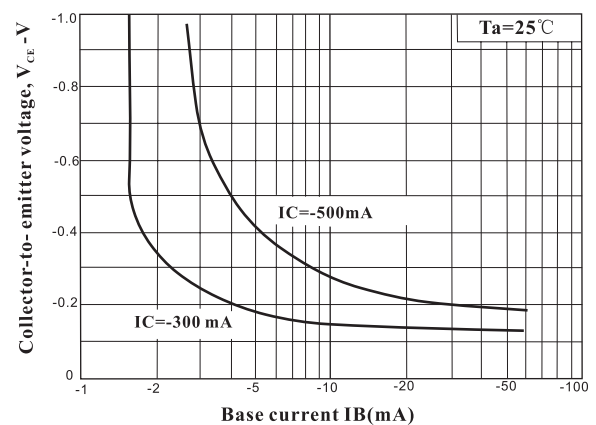
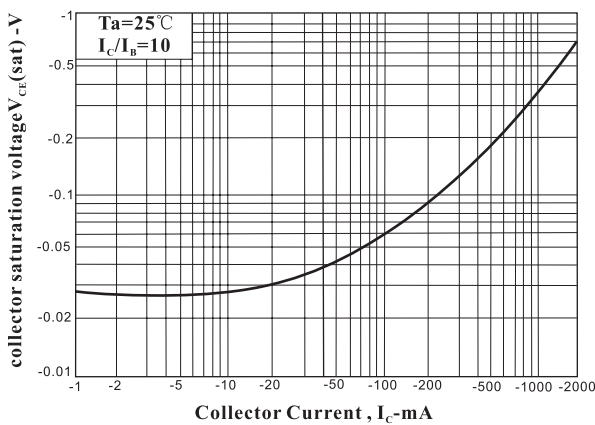
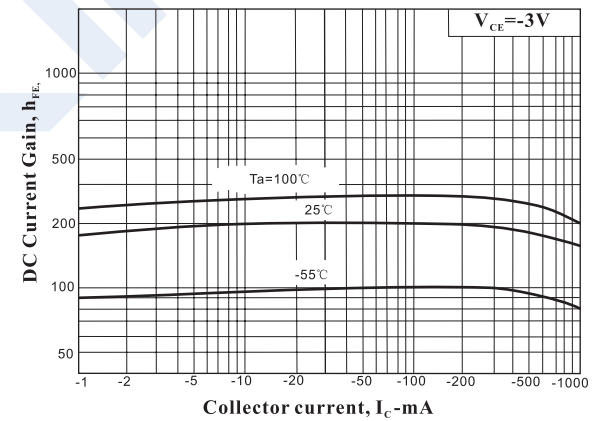
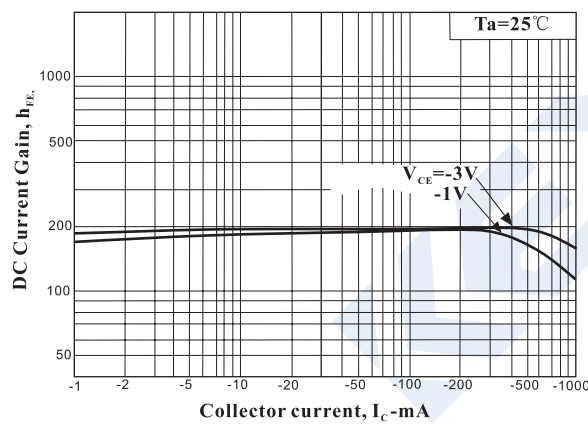
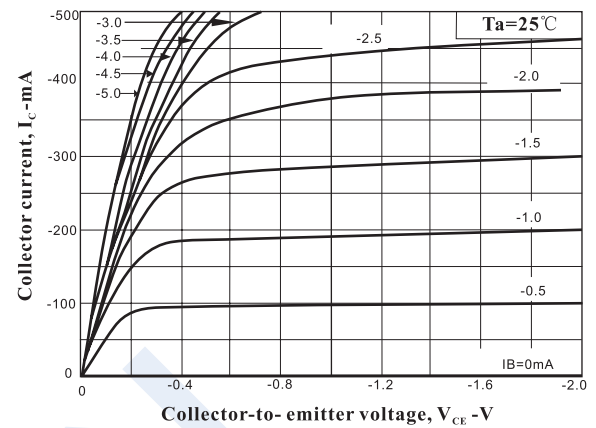
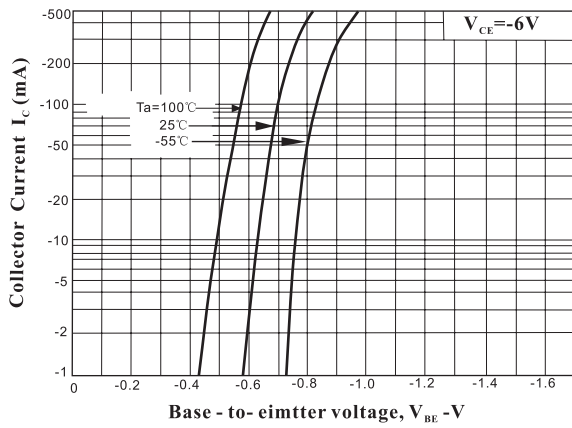
| Parameter                            | Symbol        | Test Conditions  | Min | Typ  | Max  | Unit          |
|--------------------------------------|---------------|--|-----|------|------|---------------|
| Collector- base breakdown voltage    | $V_{CBO}$     | $I_c = -50\mu\text{A}$ , $I_E = 0$                               | -40 |      |      | V             |
| Collector- emitter breakdown voltage | $V_{CEO}$     | $I_c = -1\text{mA}$ , $I_B = 0$                                  | -32 |      |      |               |
| Emitter - base breakdown voltage     | $V_{EBO}$     | $I_E = -50\mu\text{A}$ , $I_C = 0$                               | -5  |      |      |               |
| Collector-base cut-off current       | $I_{CBO}$     | $V_{CB} = -20\text{V}$ , $I_E = 0$                               |     |      | -0.5 | $\mu\text{A}$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB} = -4\text{V}$ , $I_C = 0$                                |     |      | -0.5 |               |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -500\text{mA}$ , $I_B = -50\text{mA}$                     |     | -0.2 | -0.5 | V             |
| DC current gain                      | $h_{FE}$      | $V_{CE} = -3\text{V}$ , $I_C = -0.1\text{A}$                     | 82  |      | 390  |               |
| Collector output capacitance         | $C_{ob}$      | $V_{CB} = -10\text{V}$ , $I_E = 0\text{mA}$ , $f = 1\text{MHz}$  |     | 20   | 30   | $\mu\text{F}$ |
| Transition frequency                 | $f_T$         | $V_{CE} = -5\text{V}$ , $I_E = 50\text{mA}$ , $f = 30\text{MHz}$ |     | 150  |      | MHz           |

### $h_{FE}$ Classification

| Marking  | BA*      |           |           |
|----------|----------|-----------|-----------|
| Rank     | P        | Q         | R         |
| $h_{FE}$ | 82 ~ 180 | 120 ~ 270 | 180 ~ 390 |

# 2SB1132

## Typical Characteristics



## 2SB1132

### ■ Typical Characteristics

